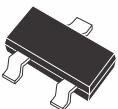


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CMPD4150

HIGH CURRENT
HIGH SPEED
SWITCHING DIODE



SOT-23 CASE

捷多邦，专业PCB打样工厂，24小时加急出货™
Central
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD4150 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

Marking code is ABA.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

	SYMBOL	UNITS
Continuous Reverse Voltage	V_R	V
Peak Repetitive Reverse Voltage	V_{RRM}	V
Continuous Forward Current	I_F	mA
Peak Repetitive Forward Current	I_{FRM}	mA
Forward Surge Current, $t_p=1 \mu\text{sec}$.	I_{FSM}	mA
Forward Surge Current, $t_p=1 \text{ sec}$.	I_{FSM}	mA
Power Dissipation	P_D	mW
Operating and Storage		
Junction Temperature	T_J, T_{stg}	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=50\text{V}$		100	nA
V_F	$I_F=1.0\text{mA}$	0.54	0.62	V
V_F	$I_F=10\text{mA}$	0.66	0.74	V
V_F	$I_F=50\text{mA}$	0.76	0.86	V
V_F	$I_F=100\text{mA}$	0.82	0.92	V
V_F	$I_F=200\text{mA}$	0.87	1.0	V
C_T	$V_R=0, f=1 \text{ MHz}$		4.0	pF
	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		4.0	ns

All dimensions in inches (mm).

